

- On page 5, line 17, please insert -- hole-- after "plug".
- On page 5, line 23, please insert -- hole-- after "plug".
- On page 6, line 1, please insert -- hole-- after "plug".
- On page 6, line 3, please insert -- hole-- after "plug".
- On page 6, line 4, please insert -- hole-- after "plug".
- On page 6, line 6, please insert -- hole-- after "plug".
- On page 6, line 9, please insert -- hole-- after "plug".
- On page 6, line 11, please insert -- hole-- after "plug".
- On page 6, line 12, please insert -- hole-- after "plug".
- On page 6, line 13, please delete "plugs", and insert -- plug hole 20 -- therefor.
- On page 7, line 1, please insert -- hole-- after "plug".
- On page 7, line 4, please insert -- hole-- after "plug".
- On page 7, line 5, please insert -- hole-- after "plug".
- On page 7, line 8, please insert -- hole-- after "plug".
- On page 7, line 9, please delete "formation of the desired", and insert -- filing of the -- therefor.

IN THE CLAIMS:

Please amend the following claims:

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1. (Twice Amended) A method of filling a feature formed in a dielectric layer, comprising:
 - a) depositing a generally conformal first barrier layer [in] on a bottom and sidewalls of the feature;
 - b) removing the first barrier layer formed on the bottom of the feature;
 - c) [sputter] depositing a second barrier layer [under conditions of a high density plasma] on substantially the bottom of the feature using a directional sputtering technique, wherein the second barrier layer comprises a material selected from a group consisting of Ta, TaN, TaSiN, TiSiN, and combinations thereof; and
 - d) depositing a metal layer in the feature, wherein the metal layer comprises copper.